

Chapter 6

Combinational CMOS Circuit and Logic Design

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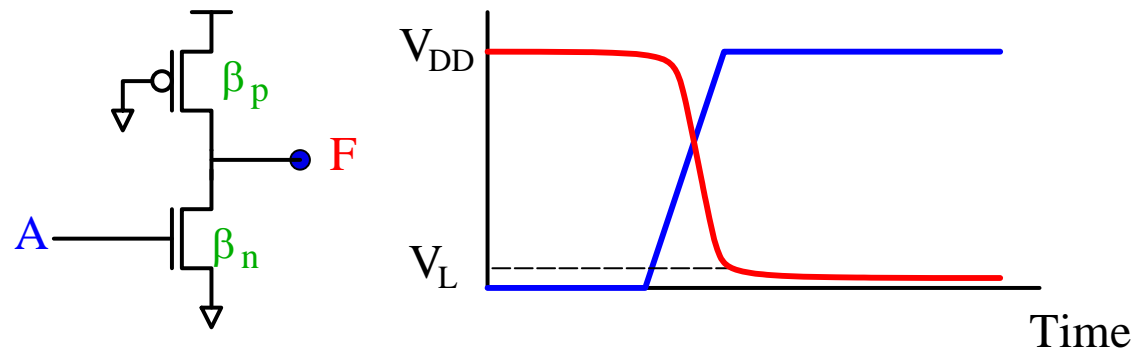
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Outline

- Advanced CMOS Logic Design
- I/O Structures

Pseudo-NMOS Logic

- A pseudo-NMOS inverter



- The low output voltage can be calculated as

$$\beta_n (V_{DD} - V_{tn}) V_L = \frac{\beta_p}{2} (V_{DD} - |V_{tp}|)^2$$

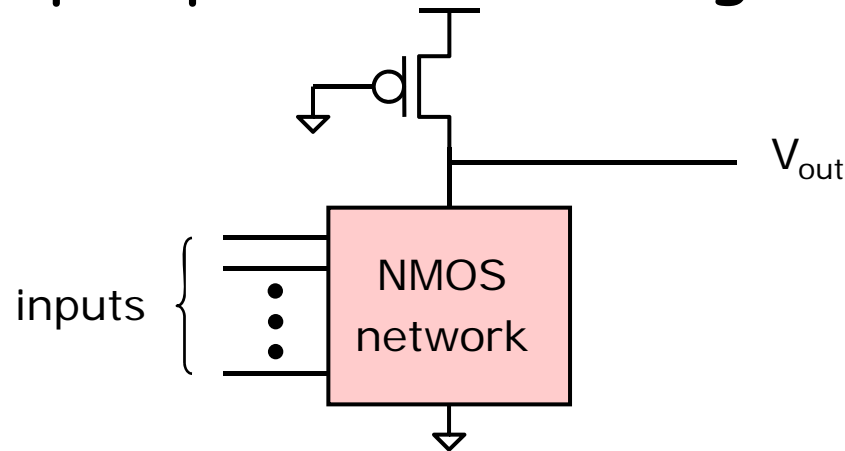
$$\text{for } V_{tn} = -V_{tp} = V_t$$

$$V_L = \frac{\beta_p}{2\beta_n} (V_{DD} - V_T)$$

- Thus V_L depends strongly on the ratio β_p / β_n
- The logic is also called ratioed logic

Pseudo-NMOS Logic

- An N-input pseudo-NMOS gate



- Features of pseudo-NMOS logic

- Advantages

- Low area cost \rightarrow only $N+1$ transistors are needed for an N -input gate
- Low input gate-load capacitance $\rightarrow C_{gn}$

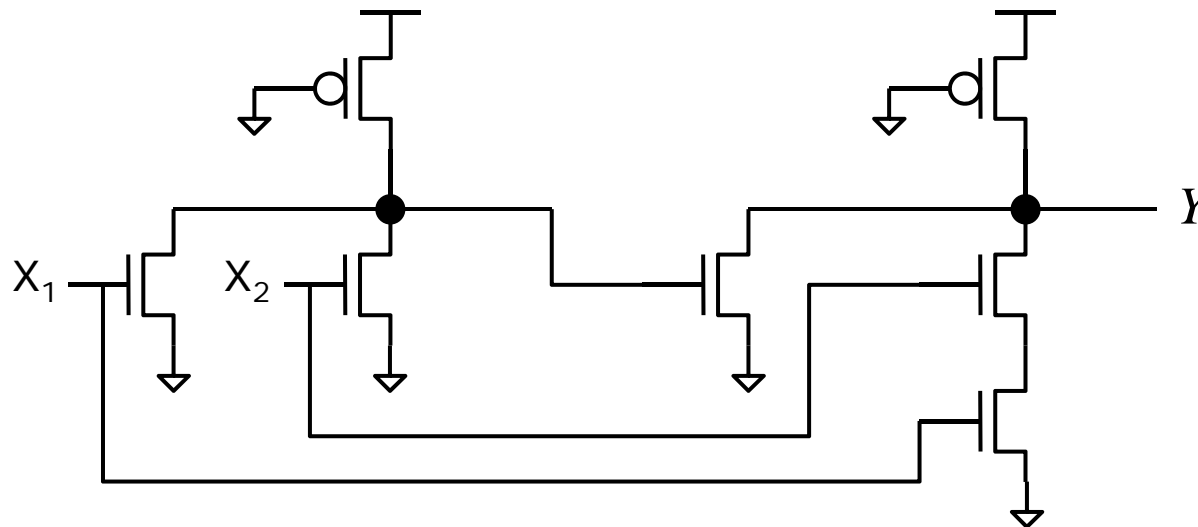
- Disadvantage

- Non-zero static power dissipation

Pseudo-NMOS XOR Gate

- An example of XOR gate realized with pseudo-NMOS logic
 - The XOR is defined by

$$Y = X_1 \oplus X_2 = X_1 \overline{X_2} + \overline{X_1} X_2 = \overline{X_1 X_2} + \overline{\overline{X_1} \overline{X_2}} = \overline{X_1 X_2 + \overline{X_1} + \overline{X_2}}$$



Choosing Transistor Sizes

□ Goals

- Noise margin
- Power consumption
- Speed

□ Noise margin

- It is affected by the low output voltage (V_L)
- V_L is determined by β_p / β_n

□ Speed

- The larger the W/L of the load transistor, the faster the gate will be, particularly when driving many other gates
- Unfortunately, this increases the power dissipation and the area of the driver network

Choosing Transistor Sizes

□ Power dissipation

- A pseudo-NMOS logic gate having a “1” output has no static (DC) power dissipation.
- However, a pseudo-NMOS gate having a “0” output has a static power dissipation
 - The static power dissipation is equal to the current of the PMOS load transistor multiplied by the power supply voltage. Thus, the power is given by

$$P_{dc} = \frac{\mu_p C_{ox}}{2} \left(\frac{W}{L} \right)_P (V_{gs} - V_{tp})^2 V_{dd}$$

- The large PMOS results in large power dissipation

□ Power-reduction methods

- Select an appropriate PMOS
- Increase the bias voltage of PMOS

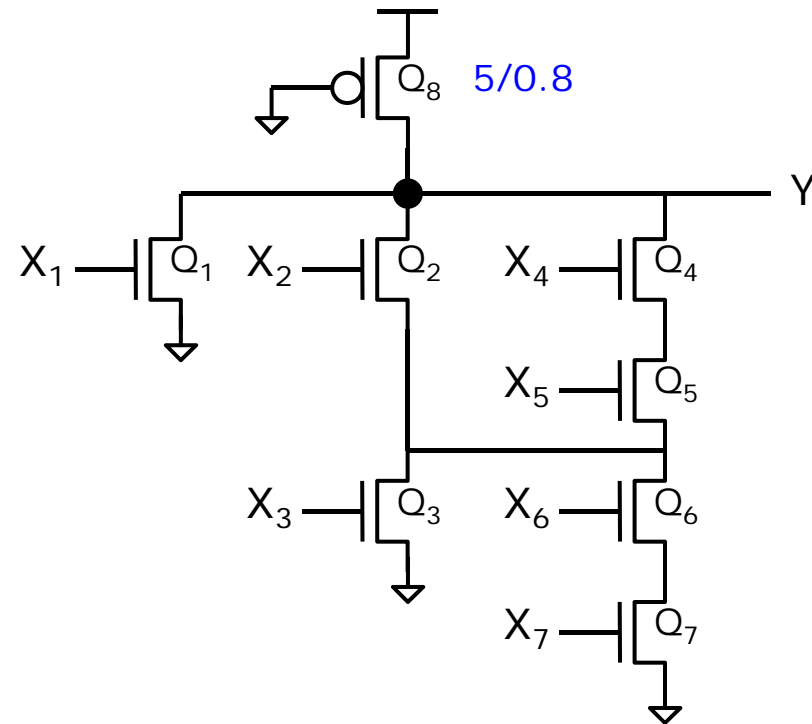
Choosing Transistor Sizes

- A simple procedure for choosing transistor sizes of pseudo-NMOS logic gates
 - The relative size (W/L) of the PMOS load transistor is chosen as a compromise between speed and size versus power dissipation
 - Once the size of the load transistor has been chosen, then a simple procedure can be used to choose the W/L s of the NMOS transistors in the NMOS network
 - Let $(W/L)_{eq}$ be equal to one-half of the W/L of the PMOS load transistor
 - For each transistor Q_i , determine the maximum number of drive transistors it will be in series, for all possible inputs. Denote this number n_i .
 - Take $(W/L)_i = n_i(W/L)_{eq}$

An Example

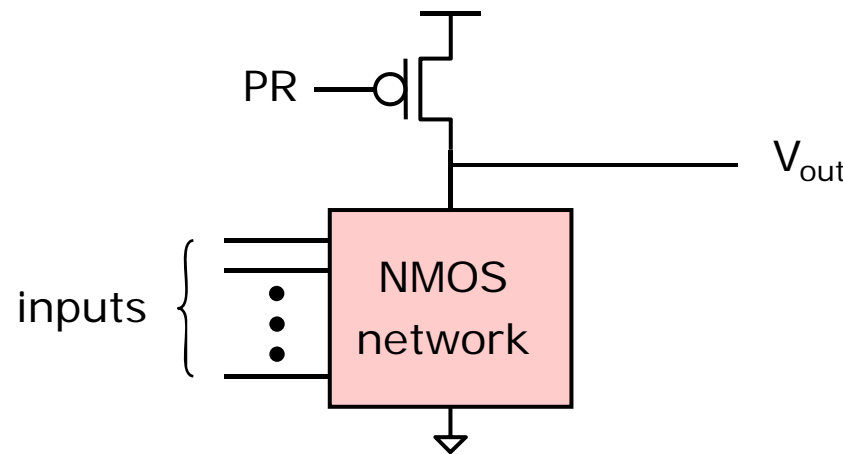
- Choose appropriate sizes for the pseudo-NMOS logic gate shown below
 - $(W/L)_8$ is $5\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
 - $(W/L)_{eq}$ is $(5/0.8)/2=3.125$
 - Gate lengths of drive transistors are taken at their minimum $0.8\text{ }\mu\text{m}$
 - Thus we can obtain

Transistor	Size
Q_1	$2.5\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_2	$5.0\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_3	$5.0\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_4	$10\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_5	$10\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_6	$10\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$
Q_7	$10\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$



Dynamic Logic

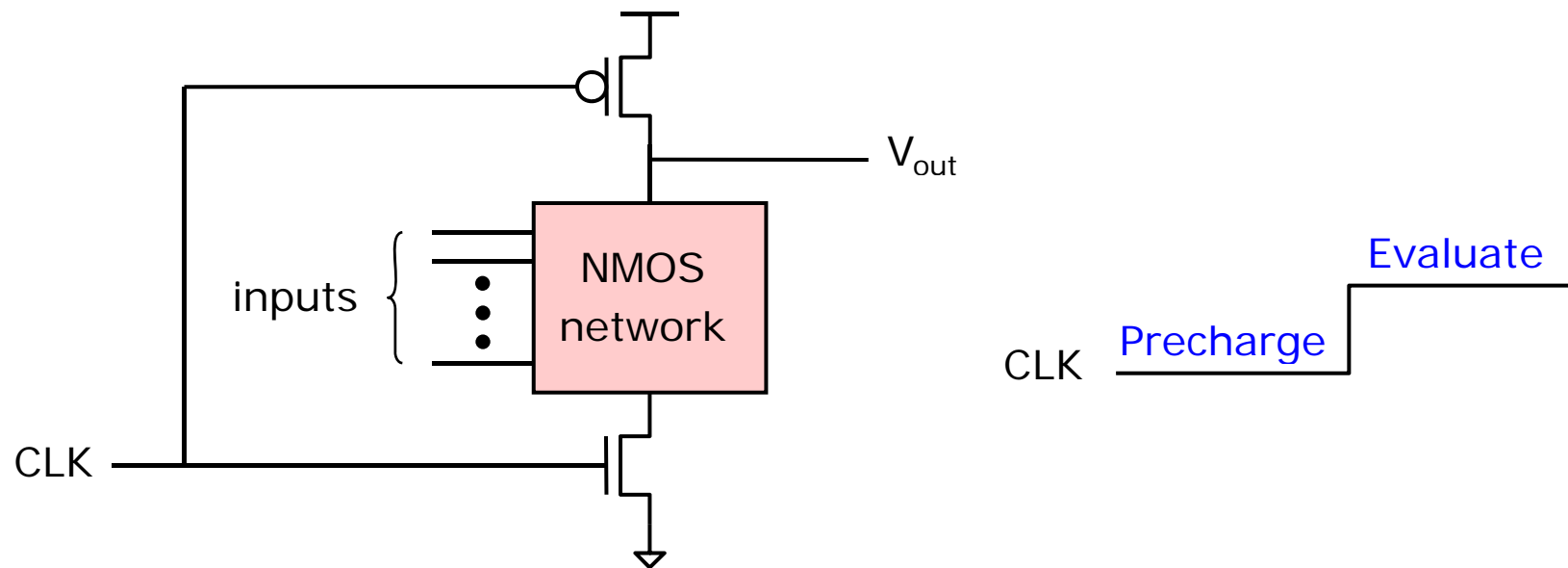
- To eliminate the static power dissipation of pseudo-NMOS logic
 - An alternative technique is to use *dynamic precharging* called dynamic logic as shown below



- Normally, during the time the output is being precharged, the NMOS network should not be conducting
 - This is usually not possible

Dynamic Logic

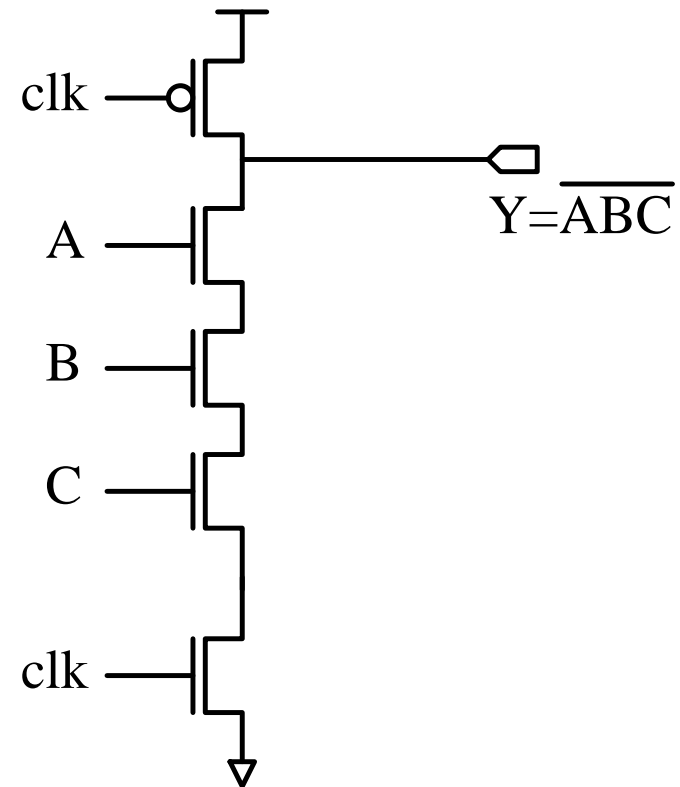
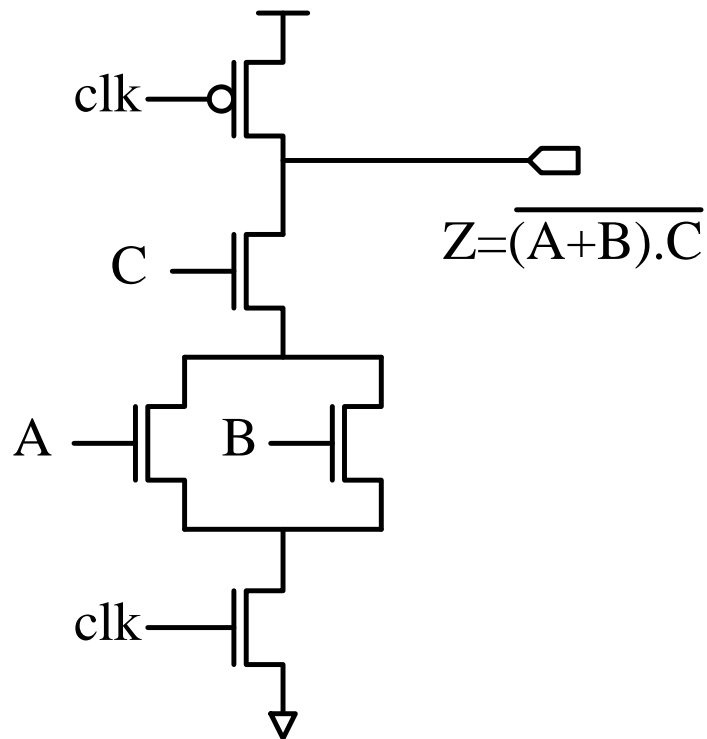
- Another dynamic logic technique



- Two-phase operation: precharge & evaluate
- This can fully eliminate static power dissipation

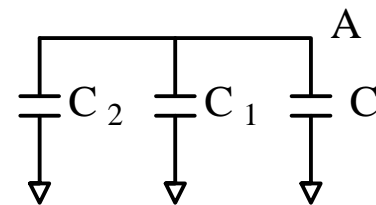
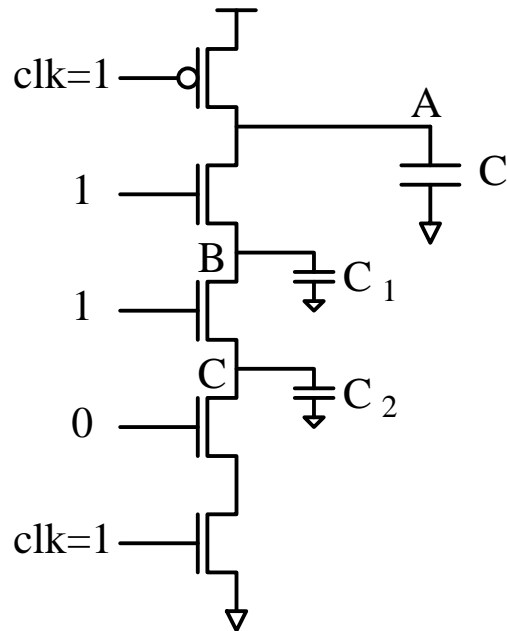
Examples of Dynamic Logic

□ Two examples



Problems of Dynamic Logic

- Two major problems of dynamic logic
 - Charge sharing
 - Simple single-phase dynamic logic can not be cascaded
- Charge sharing



charge sharing model

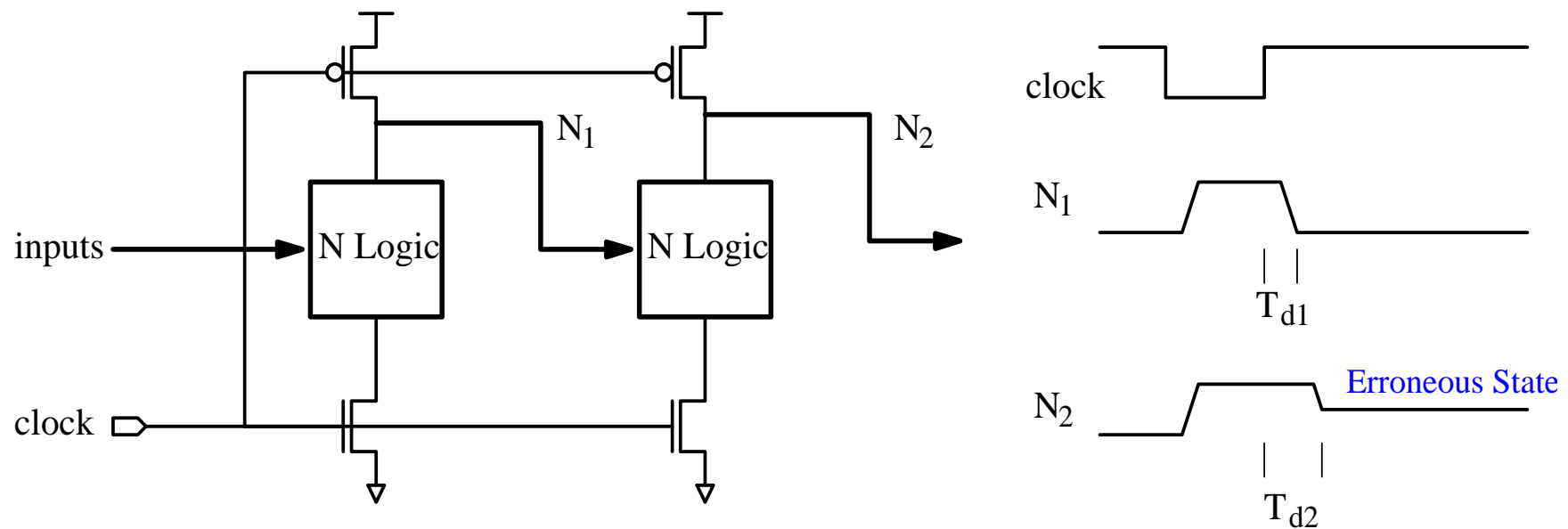
$$CV_{DD} = (C + C_1 + C_2)V_A$$

$$V_A = \frac{C}{C + C_1 + C_2}V_{DD}$$

E.g., if $C_1 = C_2 = 0.5C$
then output voltage is
 $V_{DD}/2$

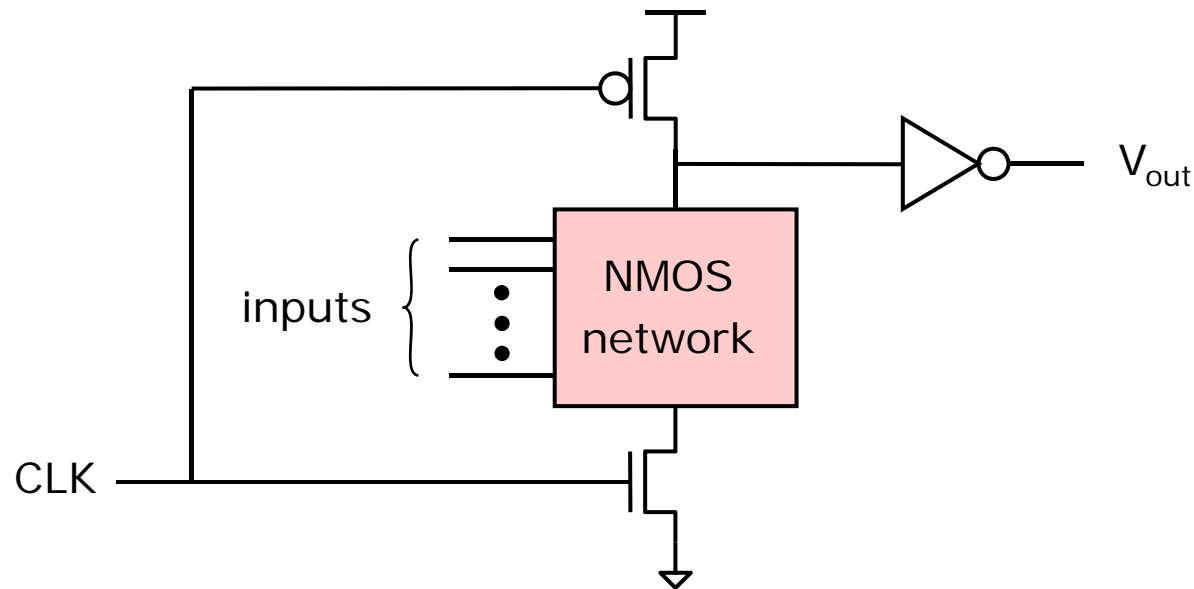
Problems of Dynamic Logic

- Simple single-phase dynamic logic can not be cascaded



CMOS Domino Logic

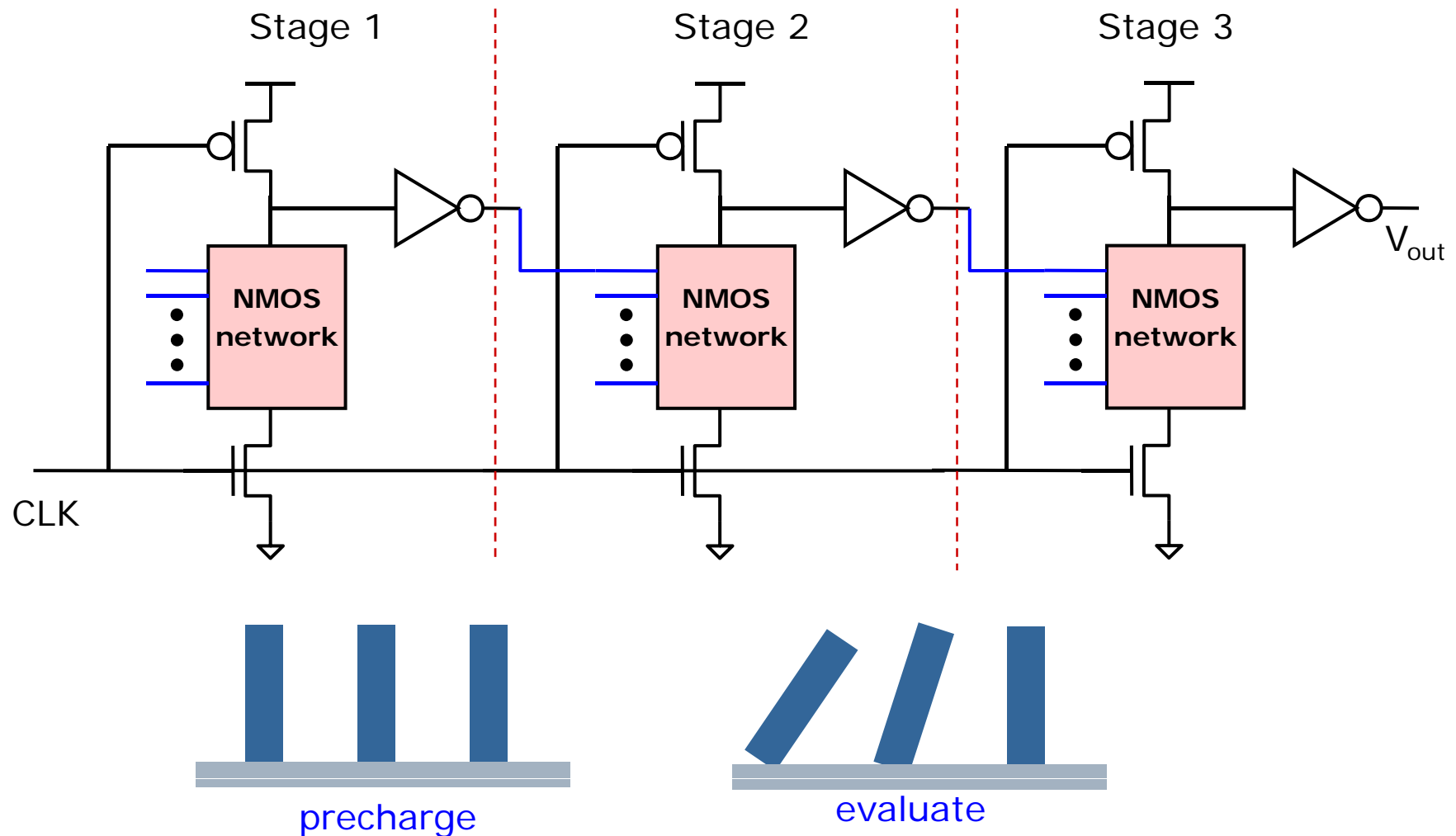
- ❑ Domino logic can be cascaded
- ❑ The basic structure of domino logic



- ❑ Some limitations of this structure
 - Each gate must be buffered
 - Only noninverting structures are possible

A Domino Cascade

- An example of cascaded domino logics

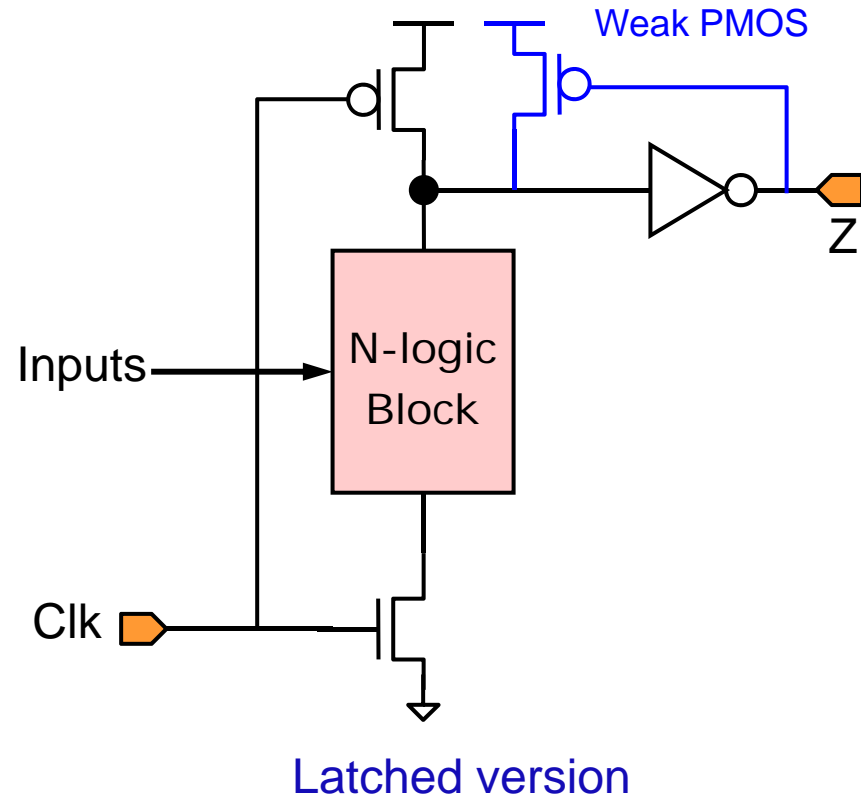
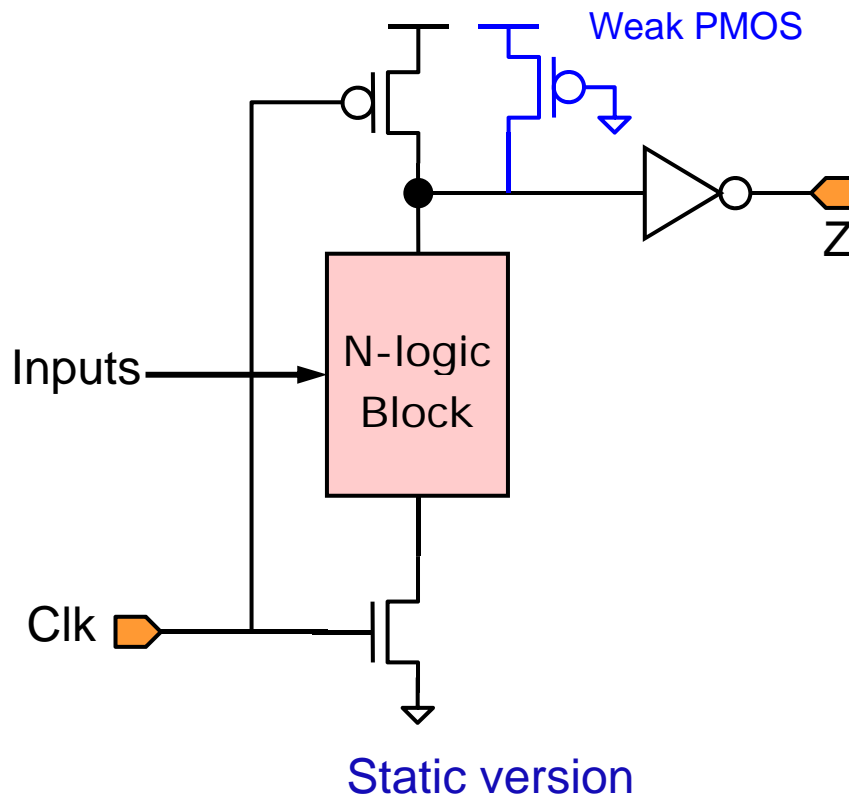


Charge-Keeper Circuits

- The domino cascade must have an evaluation interval that is long enough to allow every stage time to discharge
 - This means that charge sharing and charge leakage processes that reduce the internal voltage may be limiting factors
- Two types of modified domino logics can cope with this problem
 - Static version
 - Latched version

Charge-Keeper Circuits

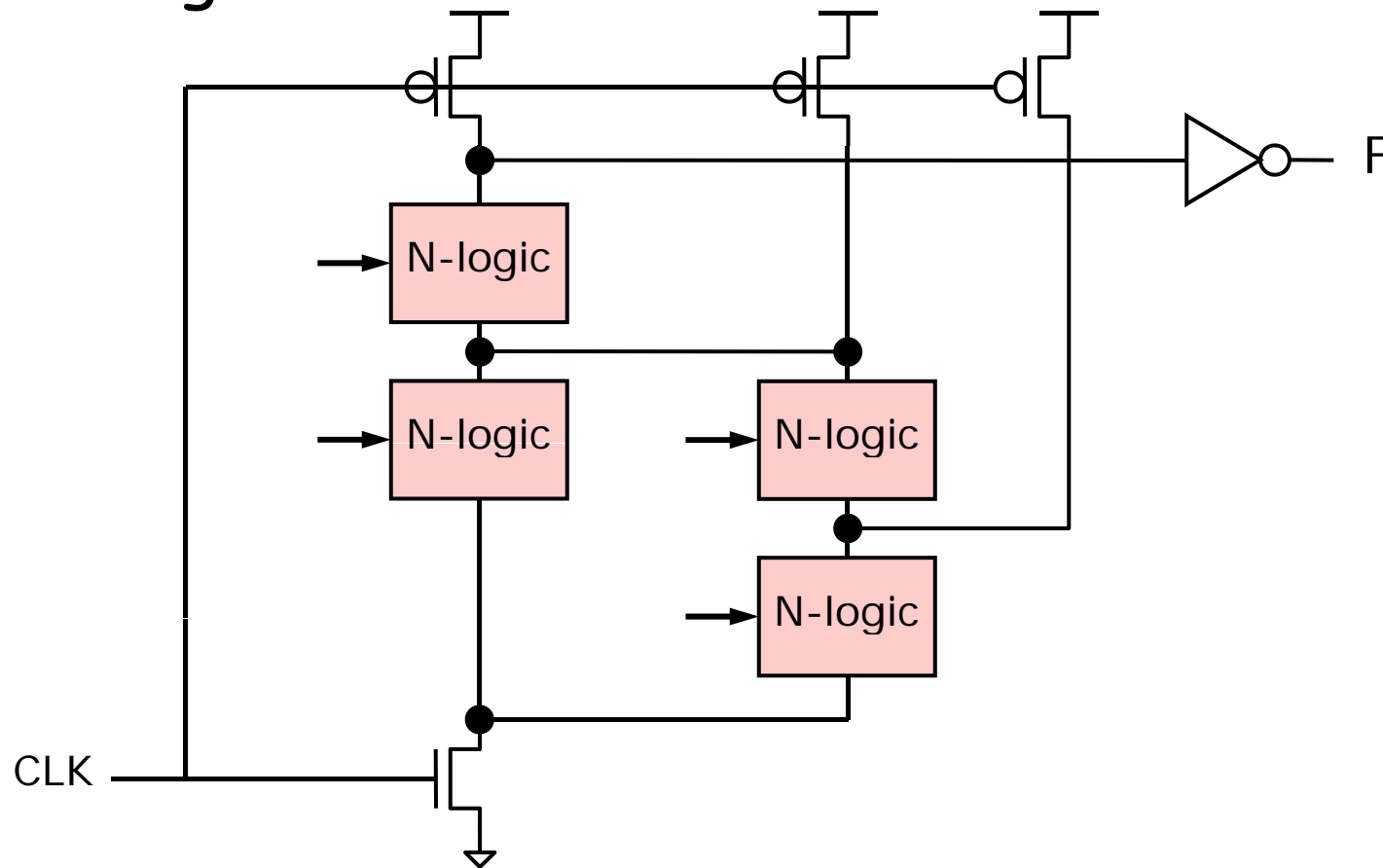
□ Modified domino logics



- The aspect ratio of the charge-keeper MOS must be small so that it does not interfere with discharge event

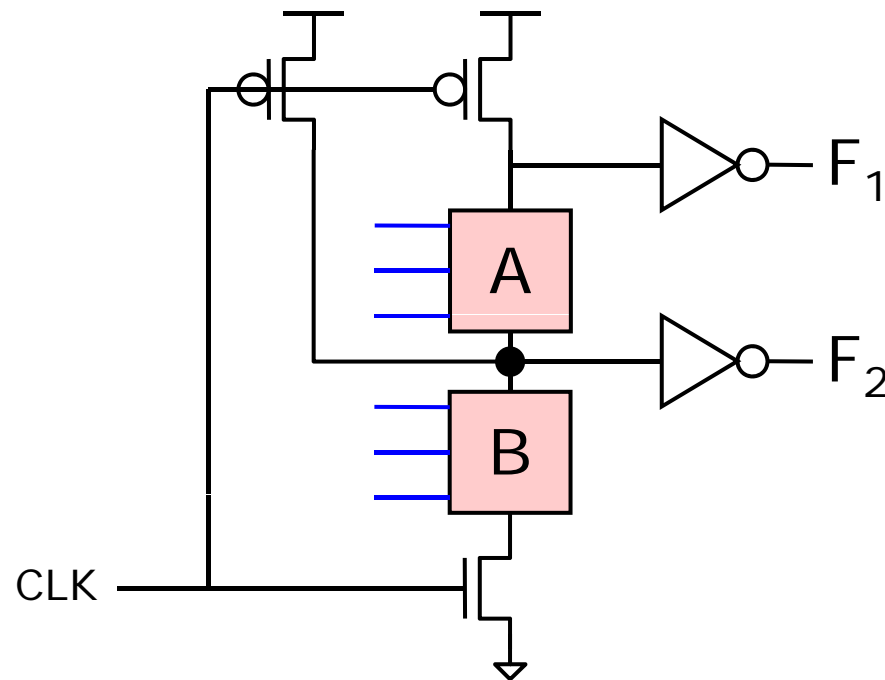
Complex Domino Gate

- In a complex domino gate, intermediate nodes have been provided with their own precharge transistor

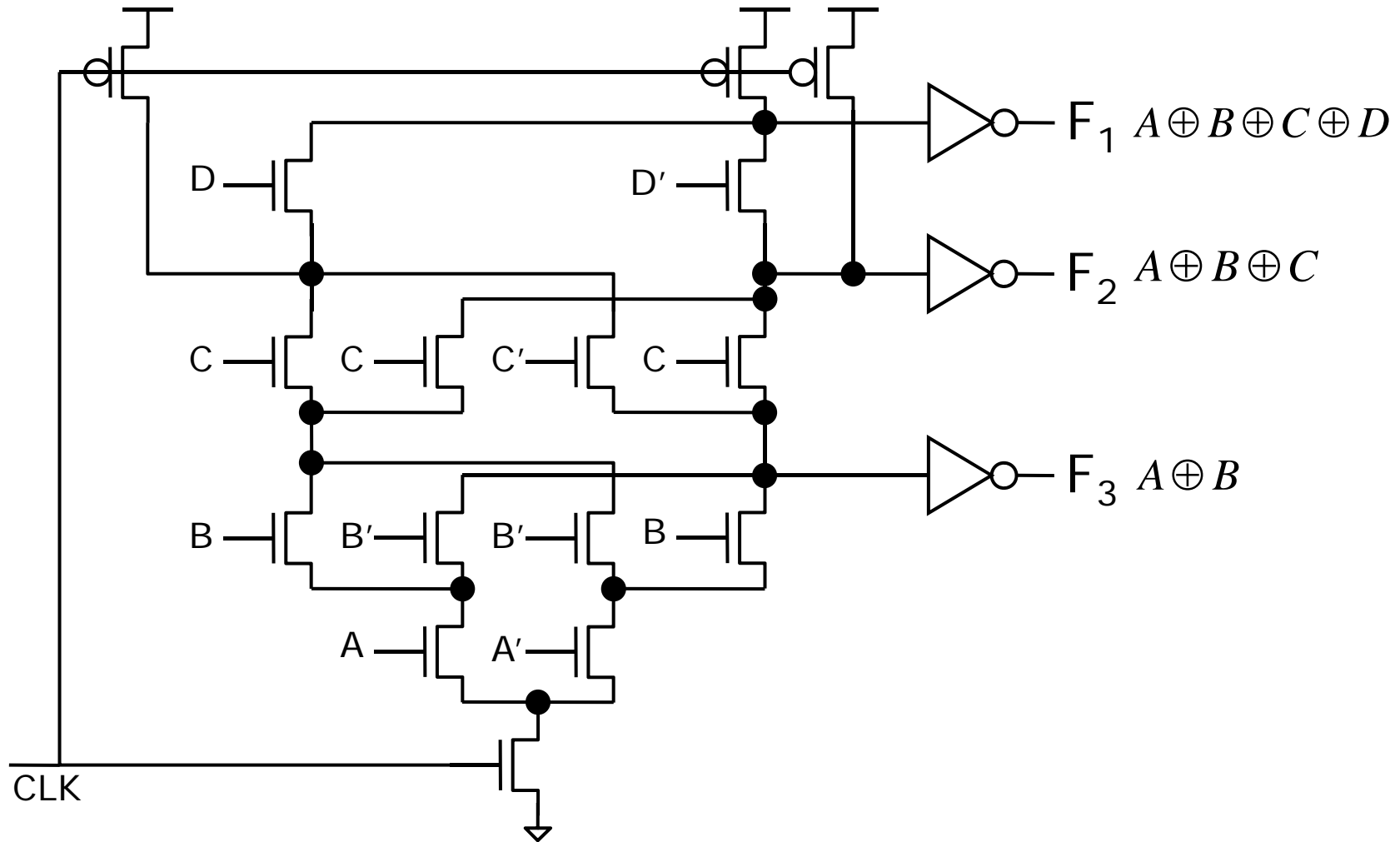


Multiple-Output Domino Logic

- ❑ Multiple-output domino logic (MODL) allows two or more outputs from a single logic gate
- ❑ The basic structure of MODL

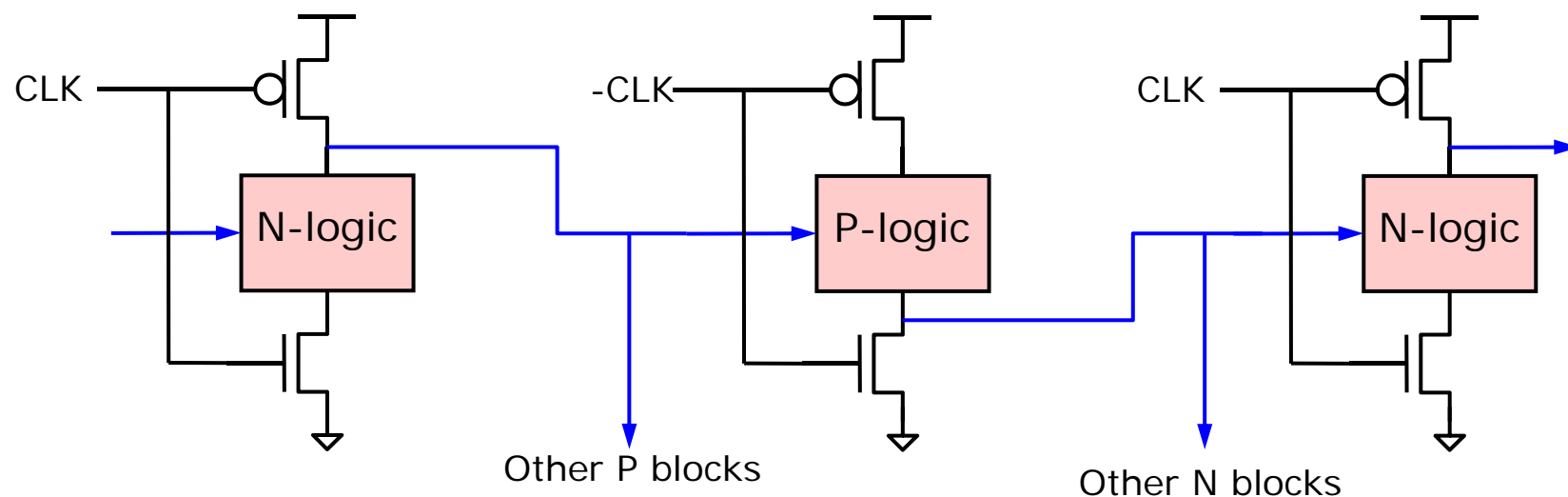


A Multiple-Output Domino Logic Gate



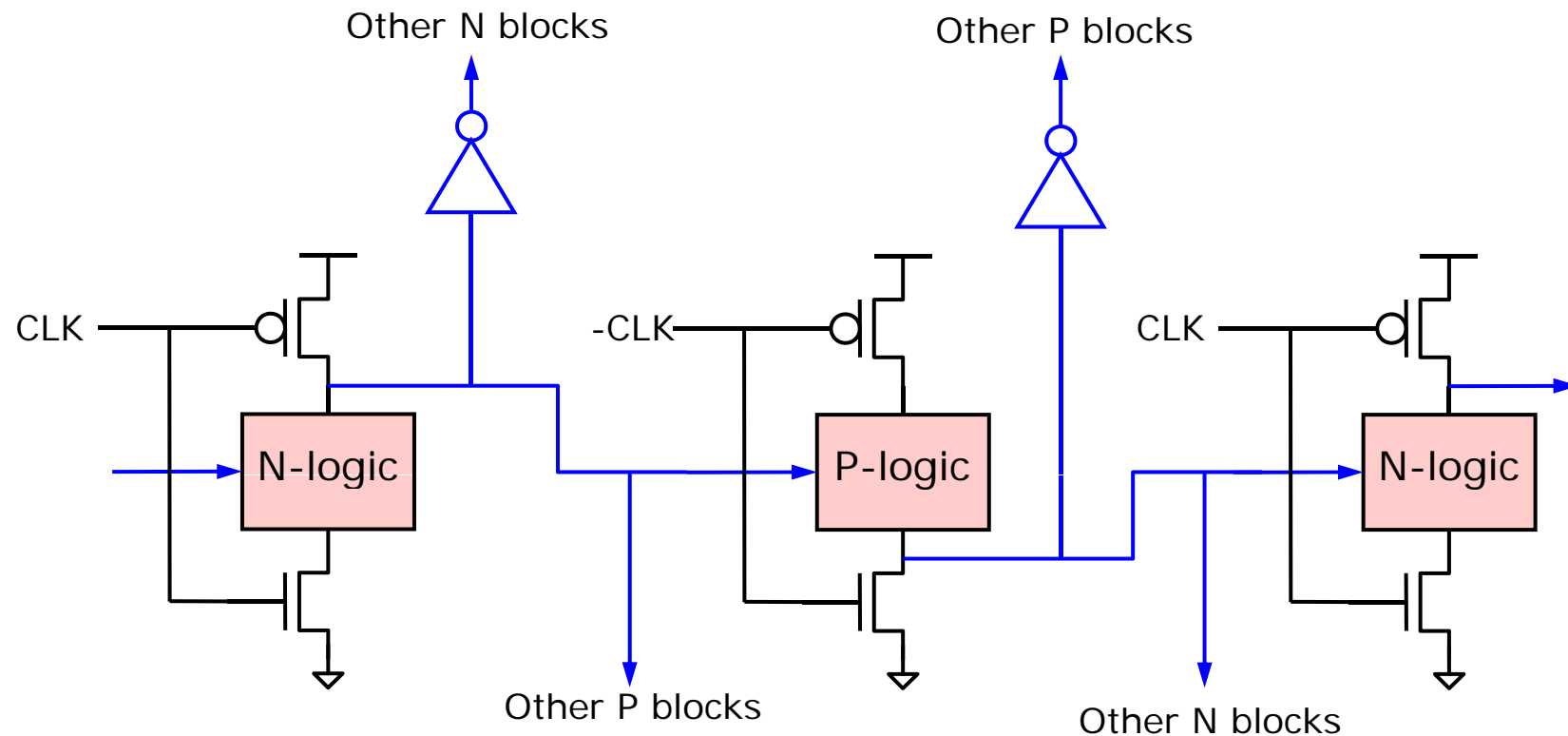
NP Domino Logic

- A further refinement of the domino logic is shown below
 - The domino buffer is removed, while cascaded logic blocks are alternately composed of P- and N-transistors



NP Domino Logic

□ NP domino logic with multiple fanouts

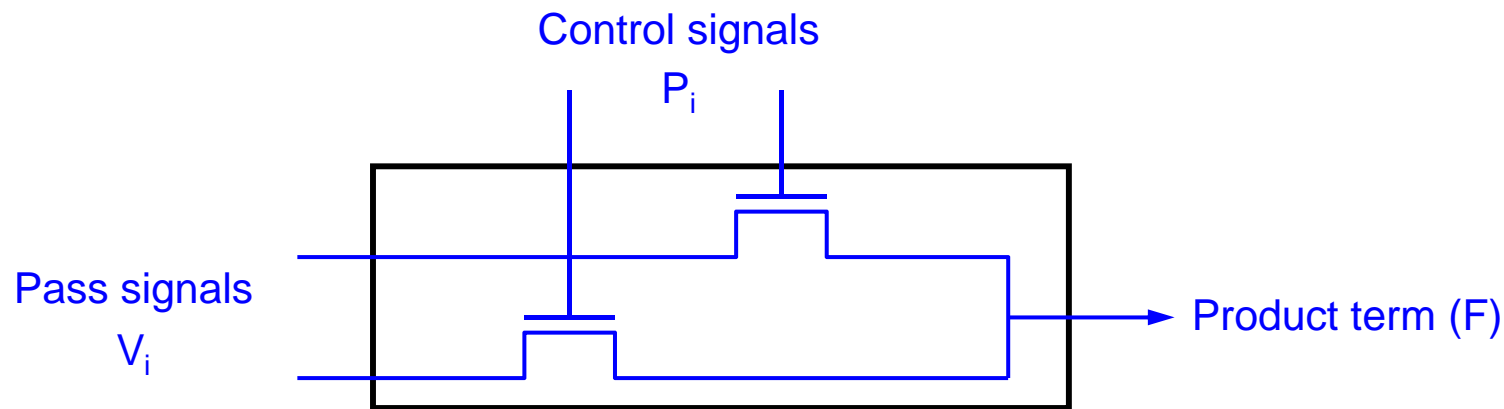


Advanced CMOS Logic Design

□ Pass-Transistor Logic

Pass-Transistor Logic

□ Model for pass transistor logic

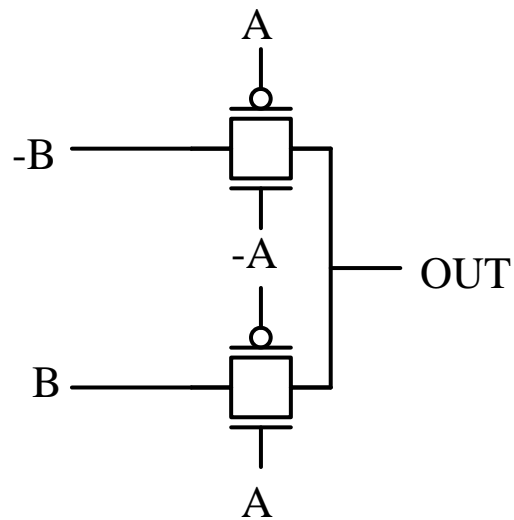


□ The product term

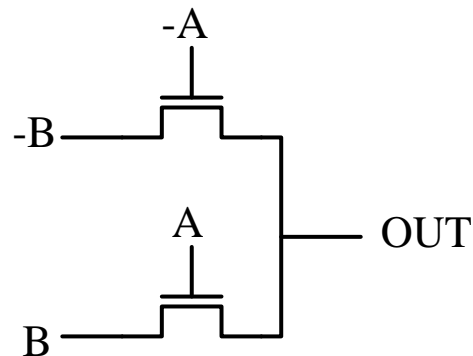
- $F = P_1 V_1 + P_2 V_2 + \dots + P_n V_n$
- The pass variables can take the values $\{0, 1, X_i, -X_i, Z\}$, where X_i and $-X_i$ are the true and complement of the i th input variable and Z is the high-impedance

Pass-Transistor Logics

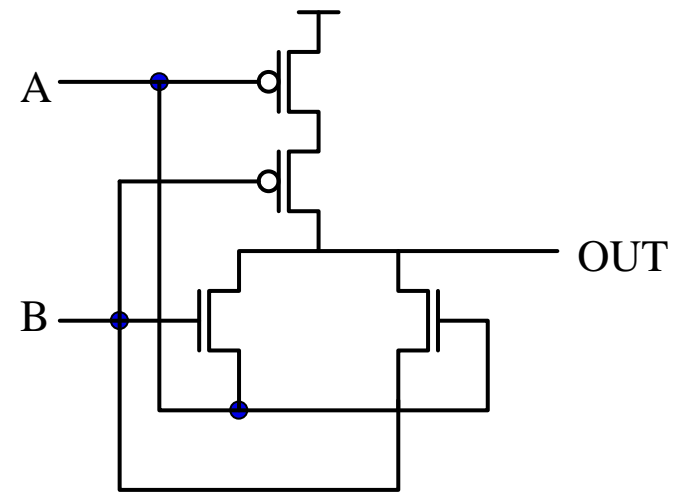
- Different types of pass-transistor logics for two-input XNOR gate implementation



Complementary



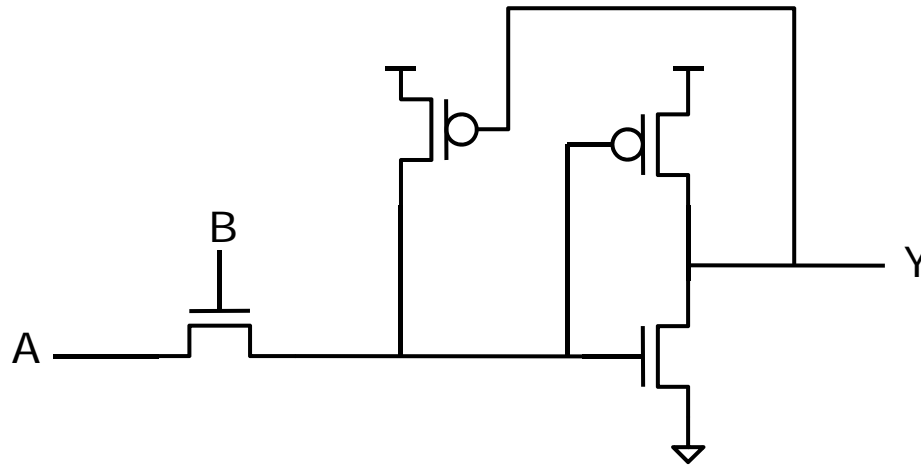
Single-polarity



Cross-coupled

Full-Swing Pass-Transistor Logic

- Modifying NMOS pass-transistor logic so full-level swings are realized



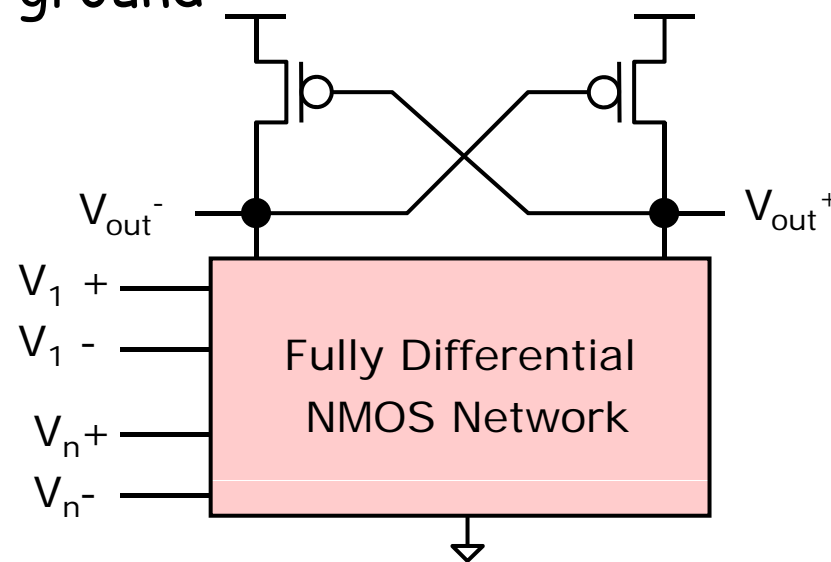
- Adding the additional PMOS has another advantages
 - It adds hysteresis to the inverter, which makes it less likely to have glitches

Differential Logic Design

- Features of the differential logic design
 - Logic inversions are trivially obtained by simply interchanging wires without incurring a time delay
 - The load networks will often consist of two cross-coupled PMOS only. This minimizes both area and the number of series PMOS transistors
- Disadvantage
 - Two wires must be used to represent every signal, the interconnect area can be significantly greater. In applications in which only a few close gates are being driven, this disadvantage is often not as significant as the advantages
- Thus differential logic circuits are often a preferable consideration

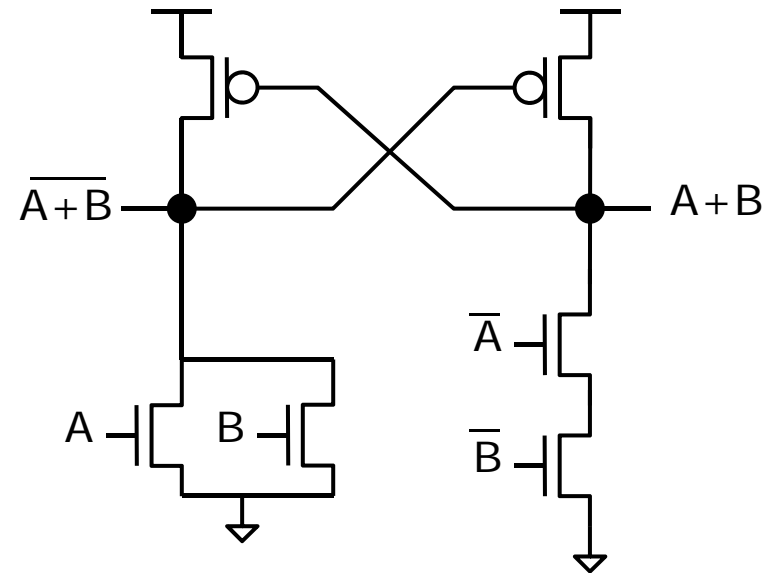
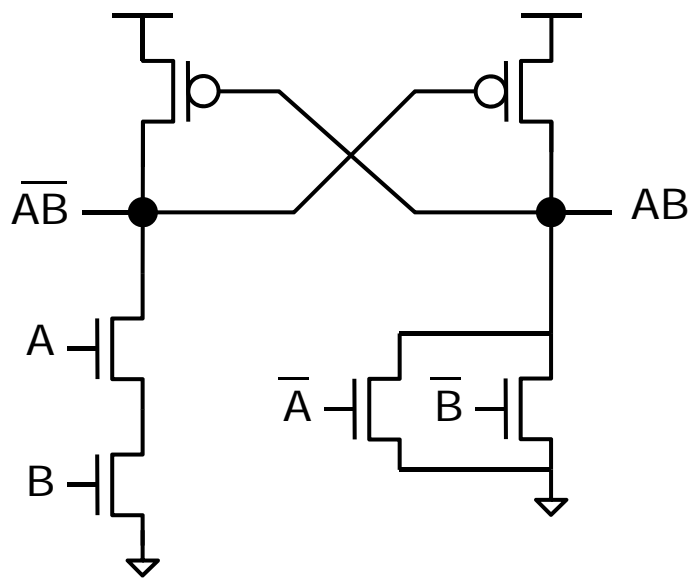
A Fully Differential Logic Circuit

- One simple and popular approach for realizing differential logic circuit is shown below
 - The inputs to the drive network come in pairs, a single-ended signal and its inverse
 - The NMOS network can be divided into two separate networks, one between the inverting output and ground, and a complementary network between the noninverting output and ground



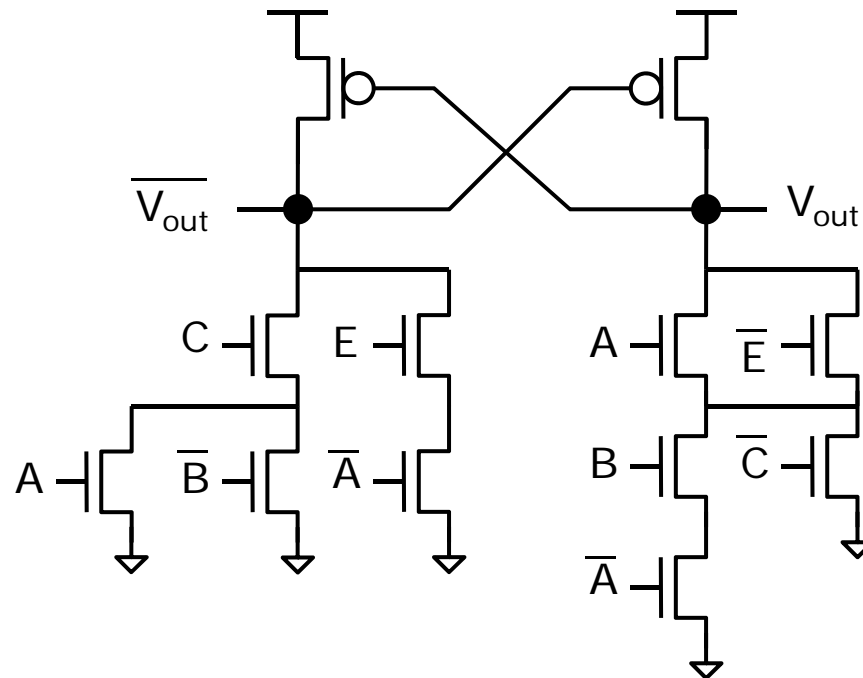
Examples

- Differential CMOS realizations of AND and OR functions



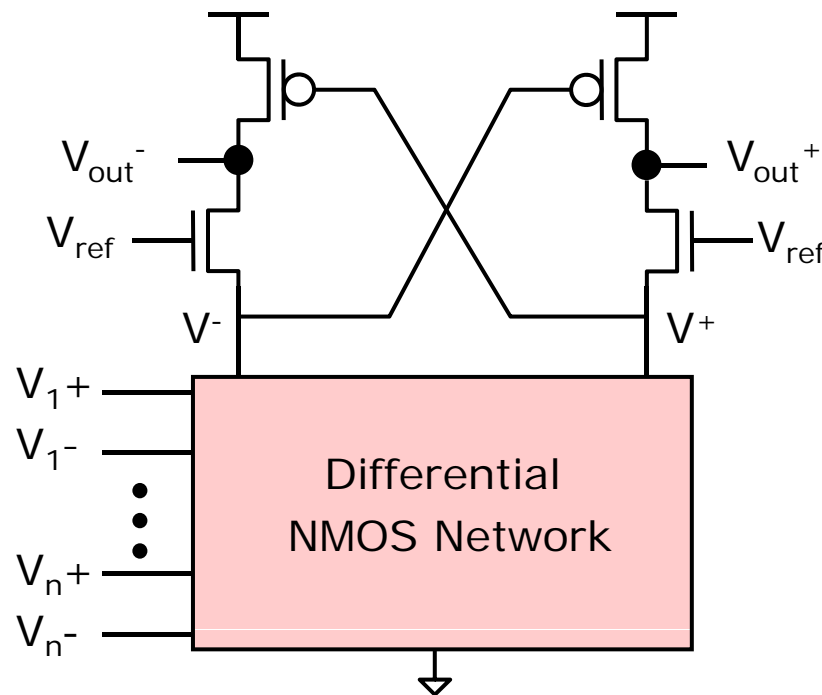
Examples

- Differential CMOS realization of the function $V_{out} = (A+B')C + A'E$



Differential Split-Level Logic

- Differential split-level (DSL) logic
 - A variation of fully differential logic
 - A compromise between a cross-coupled load with no d.c. power dissipation and a continuously-on load with d.c. power dissipation



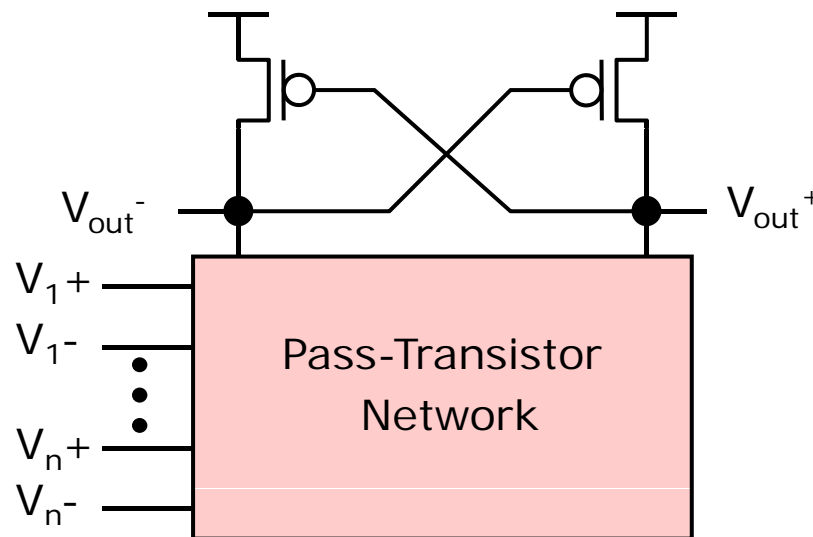
Differential Split-Level Logic

□ Features of DSL logic

- The loads have some of the features of both continuous loads and cross-coupled load
 - Both outputs begin to change immediately
 - The loads do have d.c. power dissipation, but normally much less than pseudo-NMOS gates and dynamic power dissipation
- The nodes V_+ , V_- , and all internal nodes of the NMOS network have voltage changes between greater than 0V and $V_{\text{ref}} - V_{\text{tn}}$
 - This reduced voltage swing increases the speed of the logic gates
- The maximum drain-source voltage across the NMOS transistors is reduced by about one-half
 - This greatly minimizes the short-channel effects

Differential Pass-Transistor Logic

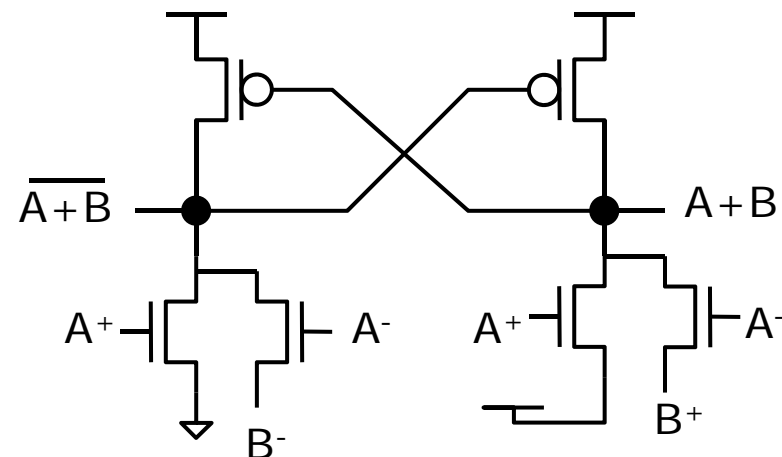
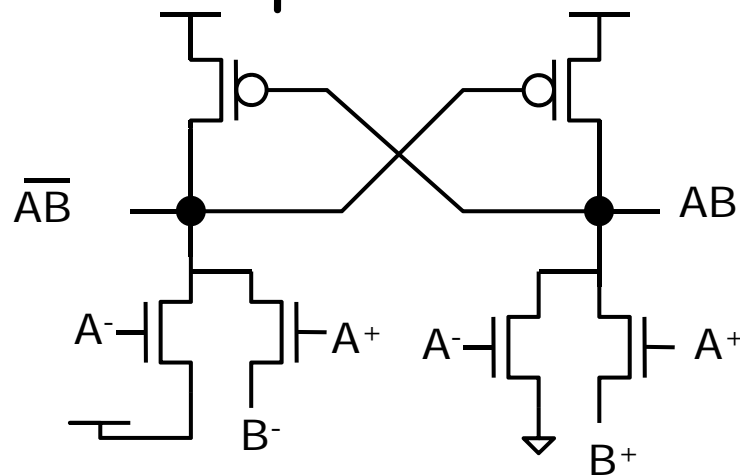
- It is not necessary to wait until one side goes to low before the other side goes high
- Pass-transistor networks for most required logic functions exist in which both sides of the cross-coupled loads are driven simultaneously
- This minimizes the time from when the inputs changes to when the low-to-high transition occurs



Differential Pass-Transistor Logic

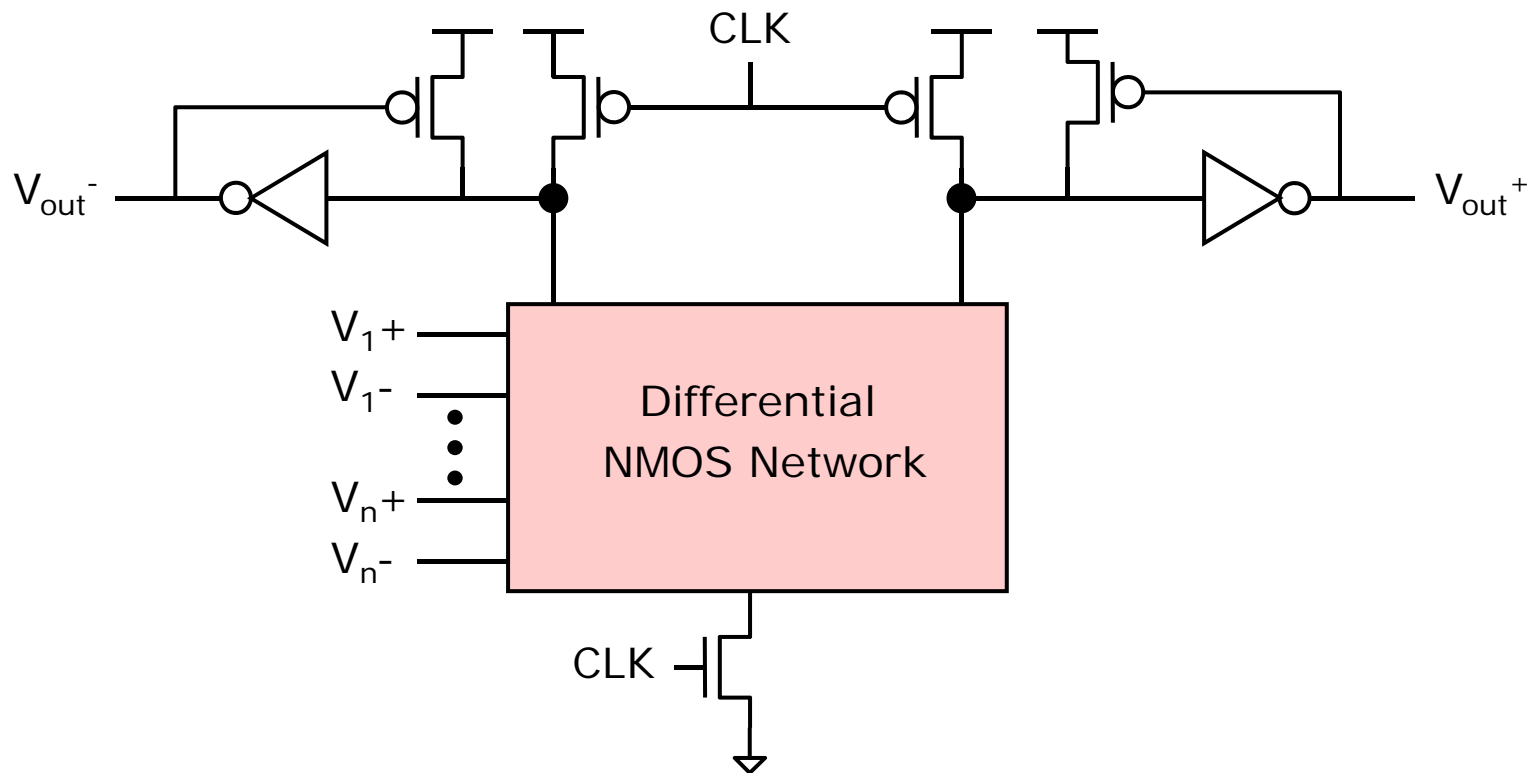
- Other features of pass-transistor logic
 - It removes the ratio requirements on the logic and has guaranteed functionality
 - The cross-coupled loads restore signal levels to full V_{dd} levels, thereby eliminating the voltage drop

- Examples:



Dynamic Differential Logic

- A differential Domino logic gate

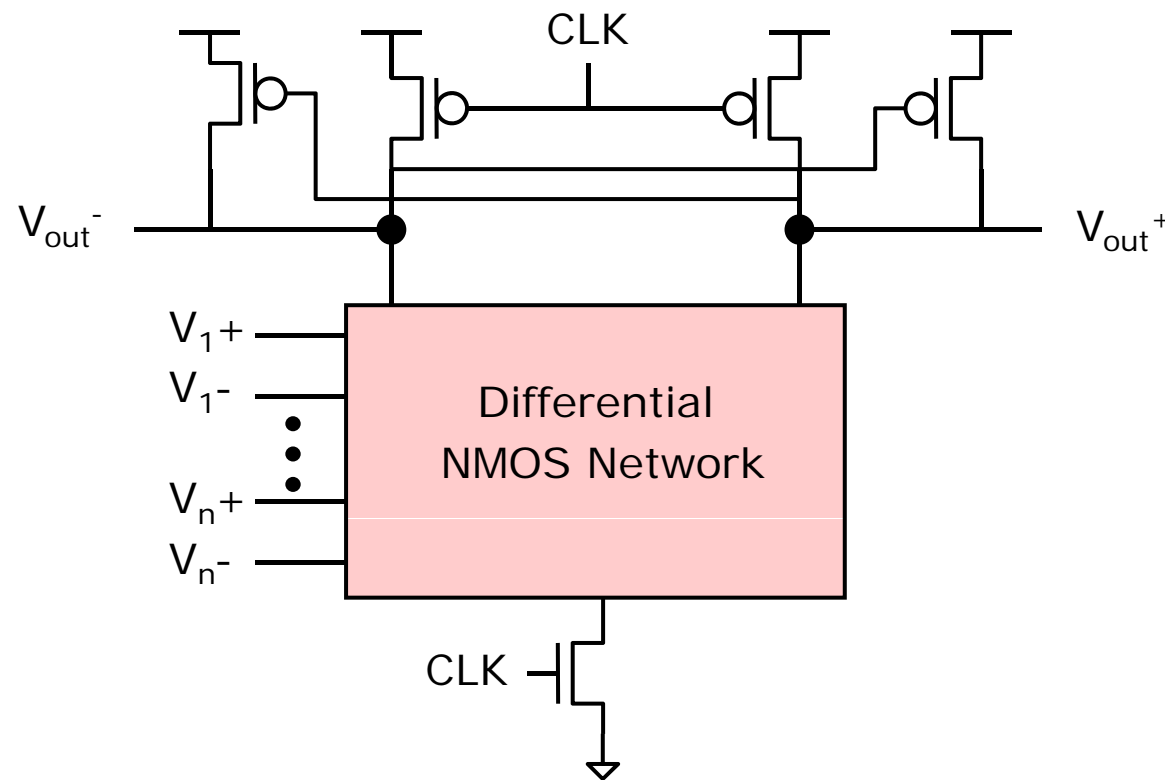


Dynamic Differential Logic

- Features of dynamic Domino logic
 - Its d.c. power dissipation is very small, whereas its speed still quite good
 - Because of the buffers at the output, its output drive capability is also very good
 - One of major limitations of Domino logic, the difficulty in realizing inverting functions, is eliminated because of the differential nature of the circuits

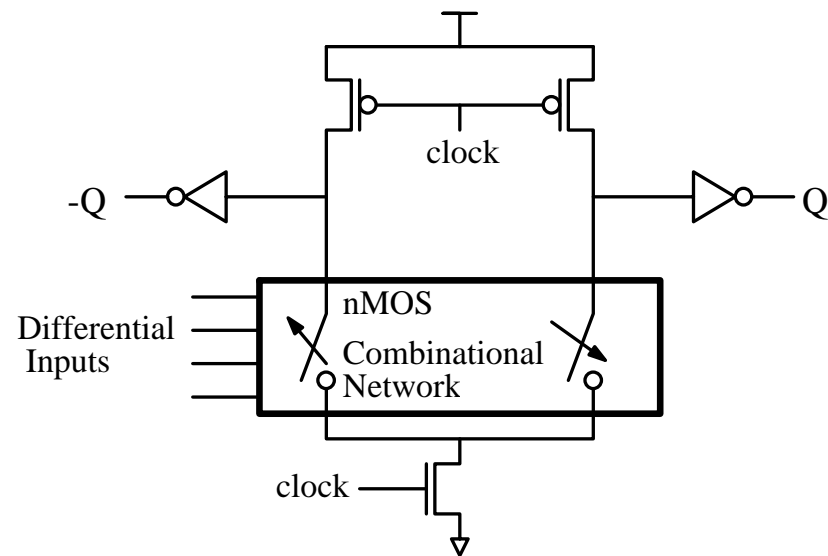
Dynamic Differential Logic

- When the fan-out is small, the inverters at the output can be eliminated and the inputs to the charge-keeper transistors can be taken from the opposite output

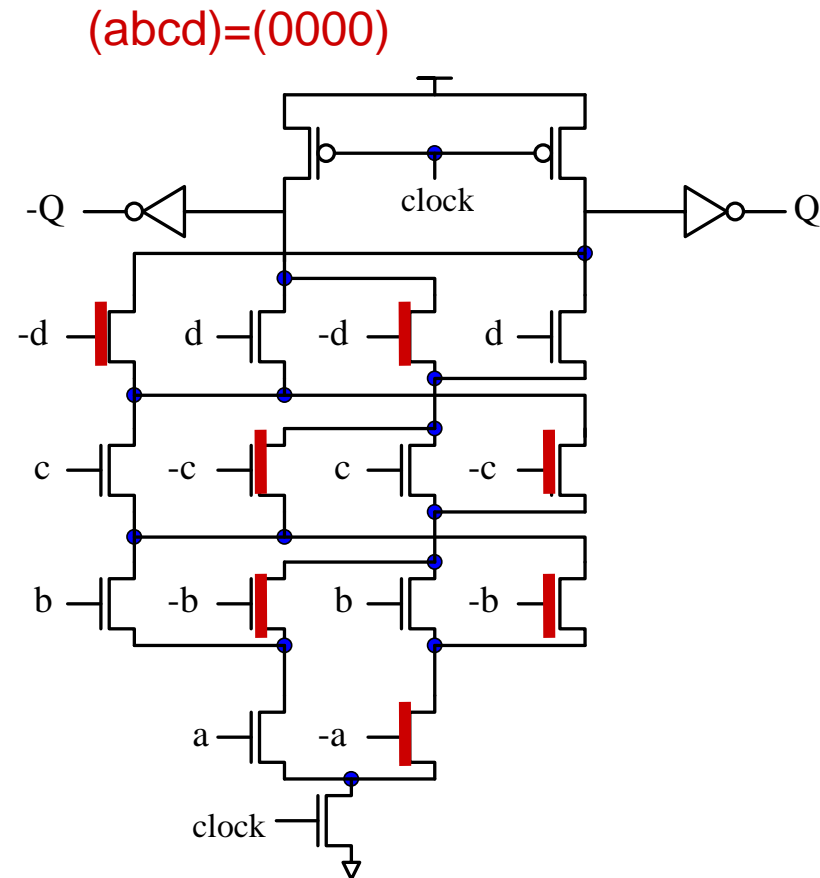


Dynamic Differential Logic

- Dynamic differential logics without charge-keeper circuit



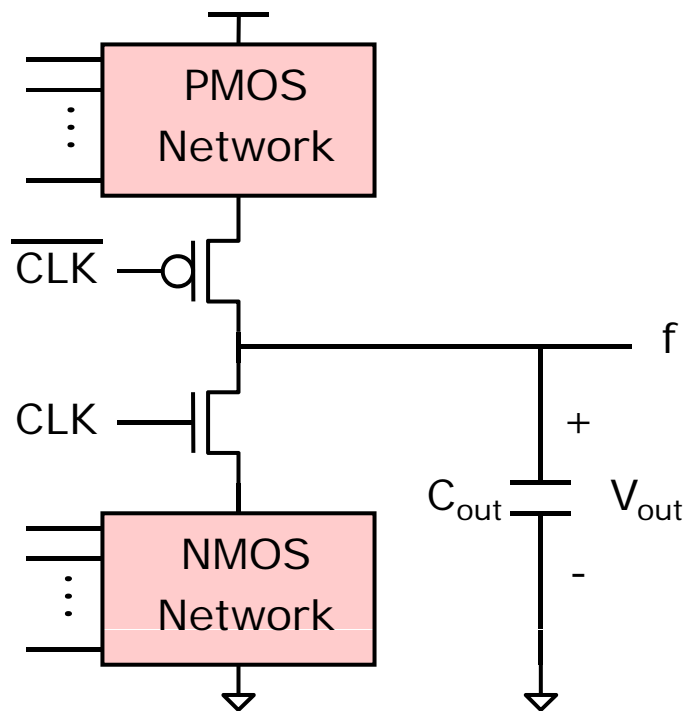
Clocked version



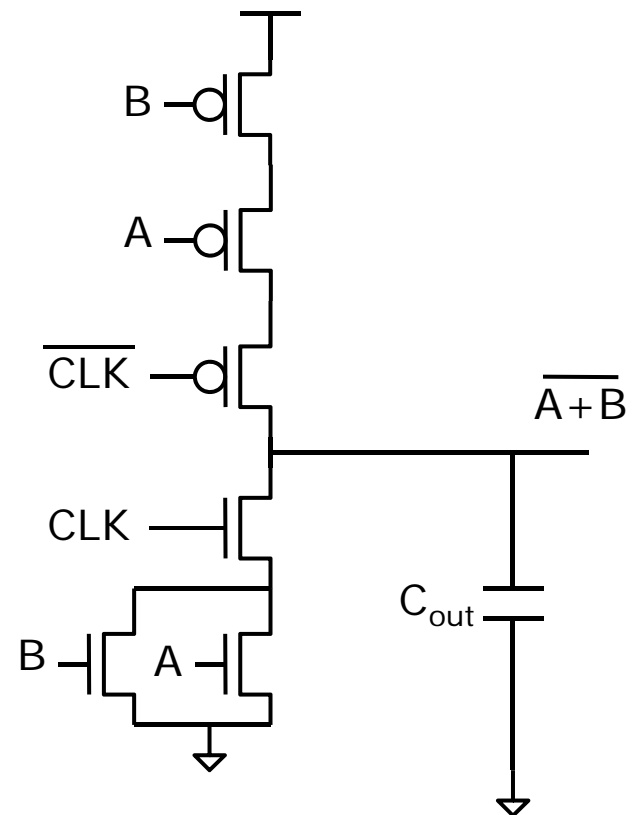
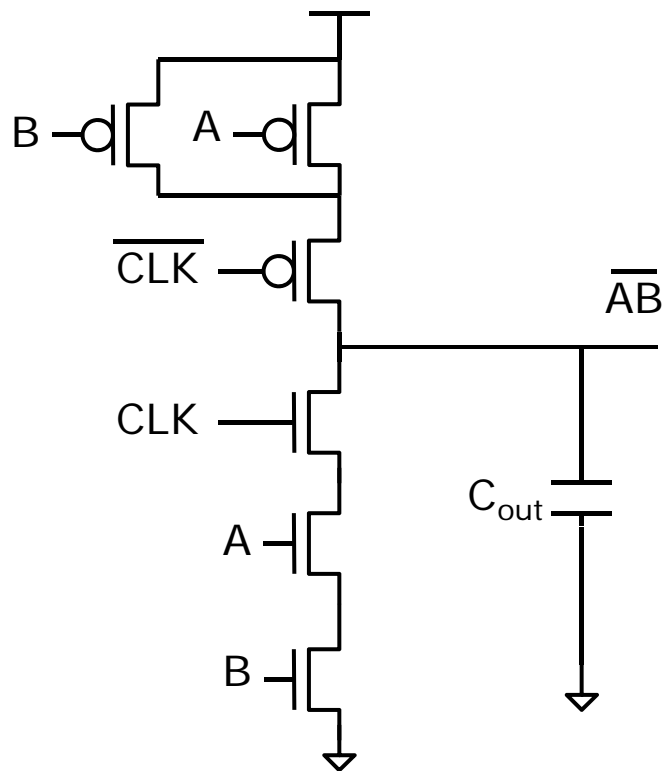
A 4-way XOR gate

Clocked CMOS (C^2 MOS)

- Structure of a C^2 MOS gate
 - Ideally, clocks are non-overlapping $\rightarrow \overline{\text{CLK}} \times \text{CLK} = 0$
 - $\text{CLK} = 1$, f is valid
 - $\text{CLK} = 0$, the output is in a high-impedance state. During this time interval, the output voltage is held on C_{out}

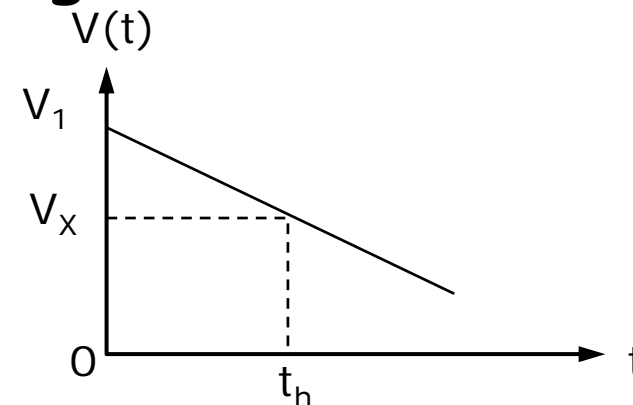
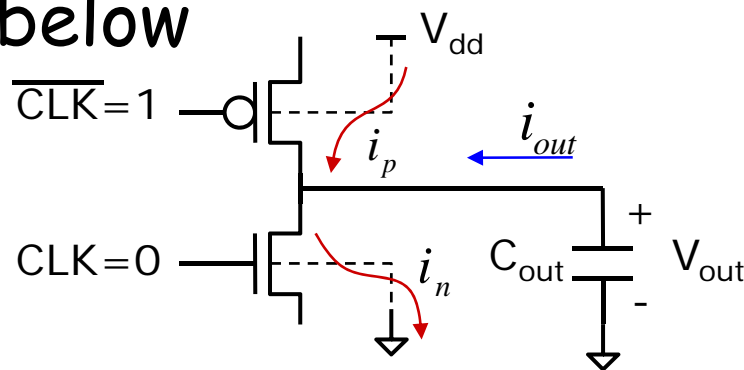


Examples of C²MOS Logic Gates



Gates

- The problem of charge leakage
 - Cause that the output node cannot hold the charge on V_{out} very long
- The basics of charge leakage are shown below



$$i_{out} = i_n - i_p = -C_{out} \frac{dV}{dt}$$

$$\Rightarrow dV = -\frac{i_{out}}{C_{out}} dt$$

Assume i_{out} is a constant I_L

$$\int_{V_1}^{V(t)} dV = -\int_0^t \frac{I_L}{C_{out}} dt \Rightarrow V(t) = V_1 - \frac{I_L}{C_{out}} t$$

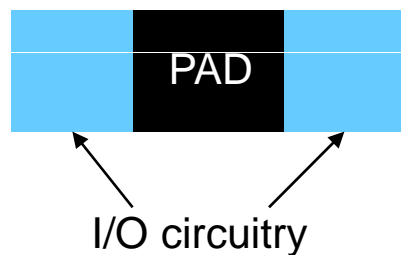
$$V(t_h) = V_1 - \frac{I_L}{C_{out}} t_h = V_X$$

$$\Rightarrow t_h = \frac{C_{out}}{I_L} (V_1 - V_X)$$

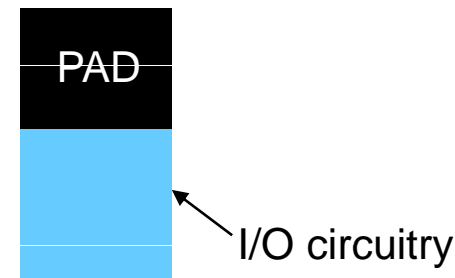
I/O Pads

- Types of pads
 - V_{dd} , V_{ss} pad
 - Input pad (ESD)
 - Output pad (driver)
 - I/O pad (ESD+driver)
- All pads need guard ring for latch-up protection
- Core-limited pad & pad-limited pad

Core-limited pad

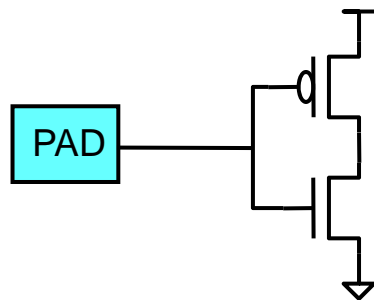


Pad-limited pad



ESD Protection

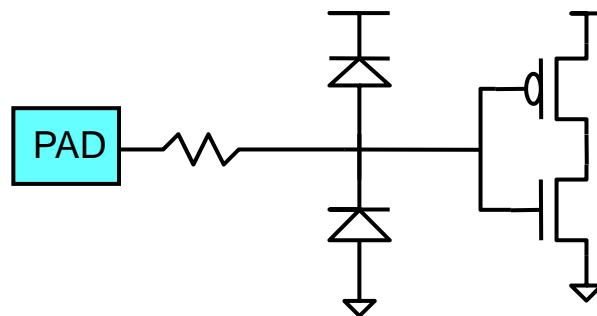
- Input pad without *electrostatic discharge* (ESD) protection



Assume $I=10\mu\text{A}$, $C_g=0.03\text{pF}$, and $t=1\mu\text{s}$

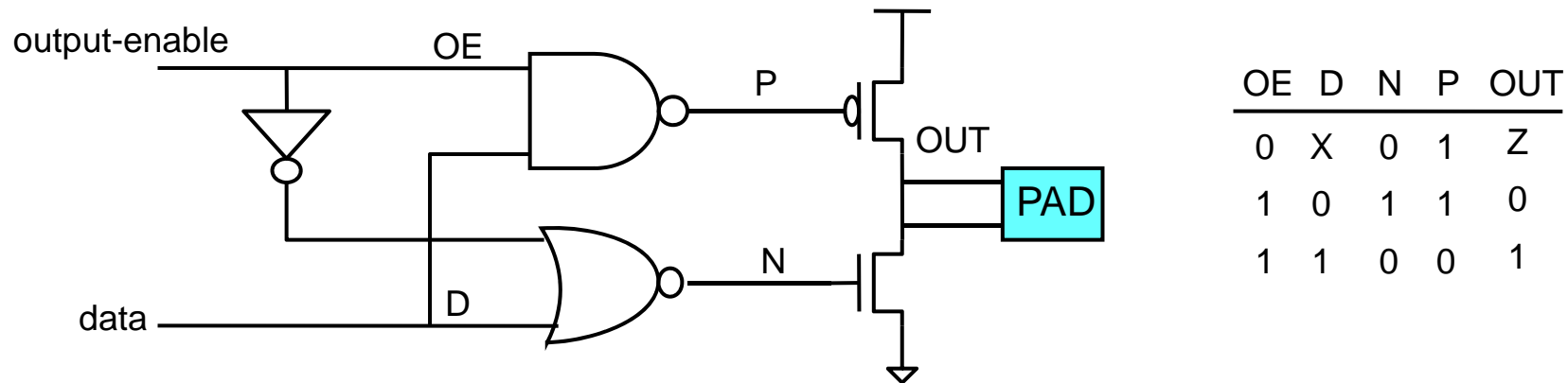
The voltage that appears on the gate is about 330volts

- Input pad with ESD protection

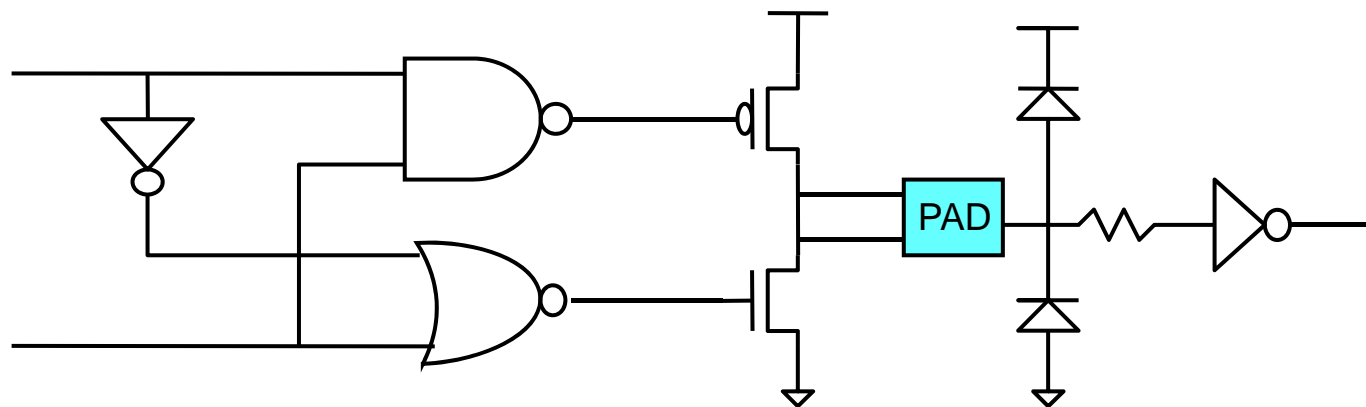


Tristate & Bidirectional Pads

□ Tristate pad

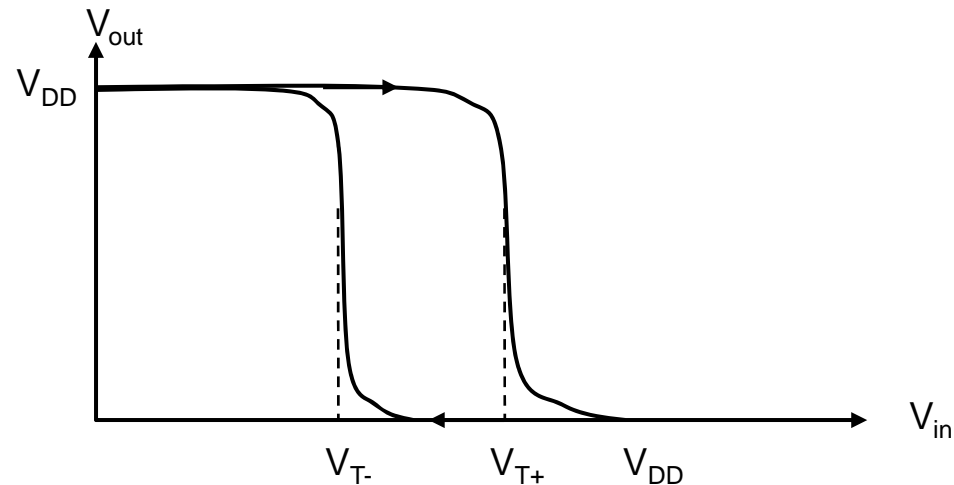


□ Bidirectional pad



Schmitt Trigger Circuit

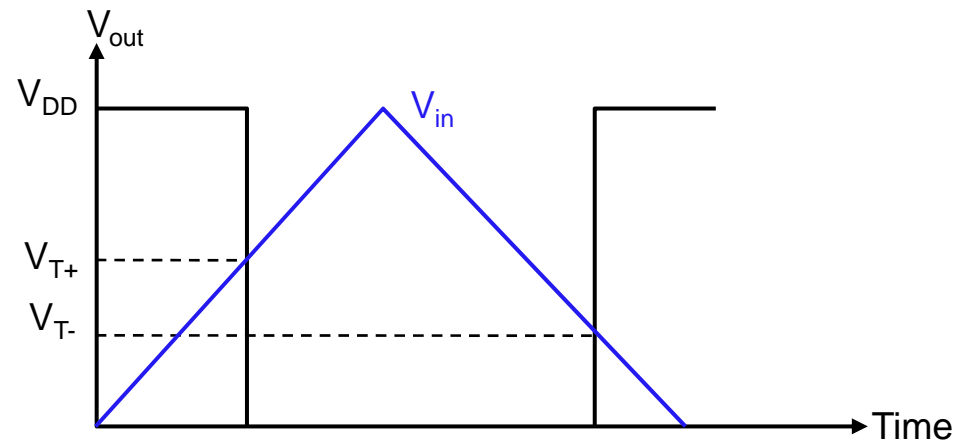
□ Voltage transfer curve of Schmitt circuit



- Hysteresis voltage $V_H = V_{T+} - V_{T-}$
- When the input is rising, it switches when $V_{in} = V_{T+}$
- When the input is falling, it switches when $V_{in} = V_{T-}$

Schmitt Trigger Circuit

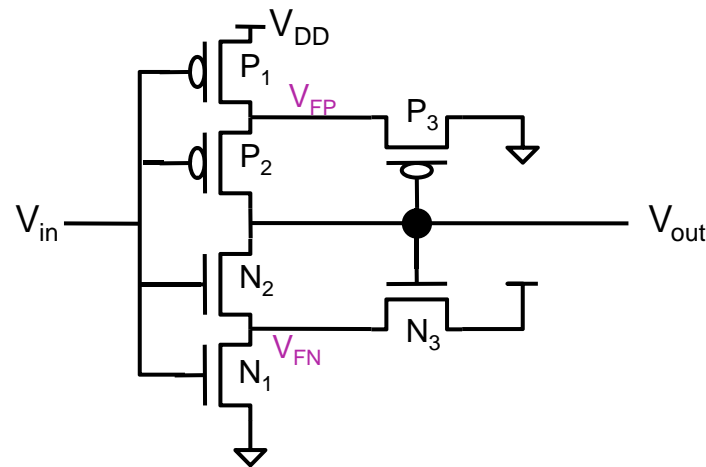
- Voltage waveform for slow input



- Schmitt trigger turns a signal with a very slow transition into a signal with a sharp transition

Schmitt Trigger Circuit

- A CMOS version of the Schmitt trigger circuit



- When the input is rising, the V_{GS} of the transistor N_2 is given by $V_{GS} = V_{in} - V_{FN}$
- When $V_{in} = V_{T+}$, N_2 enters in conduction mode which means $V_{GS2} = V_{Tn}$
- Then $V_{FN} = V_{T+} - V_{Tn}$

Summary

- The following topics have been introduced in this chapter
 - CMOS Logic Gate Design
 - Advanced CMOS Logic Design
 - Clocking Strategies
 - I/O Structures